International Rectifier

AUTOMOTIVE GRADE

AUIRF3710Z AUIRF3710ZS

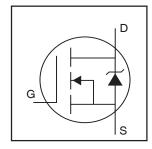
Features

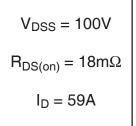
- Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

HEXFET® Power MOSFET







TO-220AB AUIRF3710Z



D²Pak AUIRF3710ZS

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units	
I _D @ T _C = 25°C Continuous Drain Current, V _{GS} @ 10V		59	Α	
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	42		
I _{DM}	Pulsed Drain Current ①	240		
P _D @T _C = 25°C	Maximum Power Dissipation	160	W	
	Linear Derating Factor	1.1	W/°C	
V _{GS}	Gate-to-Source Voltage	± 20	V	
E _{AS}	Single Pulse Avalanche Energy (Thermally limited) 2	170	mJ	
E _{AS} (tested)	Single Pulse Avalanche Energy Tested Value ®	200		
I _{AR}	Avalanche Current ①	See Fig.12a,12b,15,16	Α	
E _{AR}	Repetitive Avalanche Energy		mJ	
TJ	Operating Junction and	-55 to + 175	°C	
T _{STG}	Storage Temperature Range			
-	Soldering Temperature, for 10 seconds	300 (1.6mm from case)		
	Mounting torque, 6-32 or M3 screw ®	10 lbf•in (1.1N•m)		

Thermal Resistance

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	Parameter	Тур.	Max.	Units				
$R_{\theta JC}$	Junction-to-Case ®		0.92	°C/W				
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50						
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state)		40					

HEXFET® is a registered trademark of International Rectifier.

^{*}Qualification standards can be found at http://www.irf.com/

Static Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

	Parameter	Min.	Тур.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	100			V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient		0.10		V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance		14	18	mΩ	V _{GS} = 10V, I _D = 35A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0		4.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$
gfs	Forward Transconductance	35			S	$V_{DS} = 50V, I_{D} = 35A$
I _{DSS}	Drain-to-Source Leakage Current			20	μΑ	$V_{DS} = 100V, V_{GS} = 0V$
				250	Ī	$V_{DS} = 100V, V_{GS} = 0V, T_{J} = 125^{\circ}C$
I _{GSS}	Gate-to-Source Forward Leakage			200	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage			-200	Ī	V _{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated)

		- 0		`		,
Q_g	Total Gate Charge		82	120	nC	$I_D = 35A$
Q_{gs}	Gate-to-Source Charge		19	28		$V_{DS} = 80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge		27	40	ĺ	V _{GS} = 10V ④
t _{d(on)}	Turn-On Delay Time		17		ns	$V_{DD} = 50V$
t _r	Rise Time		77		Ī	$I_D = 35A$
t _{d(off)}	Turn-Off Delay Time		41		Î	$R_G = 6.8\Omega$
t _f	Fall Time		56			V _{GS} = 10V ④
L _D	Internal Drain Inductance		4.5		nΗ	Between lead,
						6mm (0.25in.)
Ls	Internal Source Inductance		7.5			from package
						and center of die contact
C _{iss}	Input Capacitance		2900		рF	$V_{GS} = 0V$
C _{oss}	Output Capacitance		290		ĺ	$V_{DS} = 25V$
C _{rss}	Reverse Transfer Capacitance		150			f = 1.0MHz, See Fig. 5
Coss	Output Capacitance		1130			$V_{GS} = 0V$, $V_{DS} = 1.0V$, $f = 1.0MHz$
C _{oss}	Output Capacitance		170			$V_{GS} = 0V, V_{DS} = 80V, f = 1.0MHz$
C _{oss} eff.	Effective Output Capacitance		280			$V_{GS} = 0V$, $V_{DS} = 0V$ to $80V$

Diode Characteristics

	Parameter		Тур.	Max.	Units	Conditions
Is	Continuous Source Current			59		MOSFET symbol
	(Body Diode)				Α	showing the
I _{SM}	Pulsed Source Current			240		integral reverse
	(Body Diode) ①					p-n junction diode.
V_{SD}	Diode Forward Voltage			1.3	V	$T_J = 25$ °C, $I_S = 35A$, $V_{GS} = 0V$ ④
t _{rr}	Reverse Recovery Time		50	75	ns	$T_J = 25^{\circ}C$, $I_F = 35A$, $V_{DD} = 25V$
Q _{rr}	Reverse Recovery Charge		100	160	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsi	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)			

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by T_{Jmax} , starting $T_J = 25$ °C, L = 0.27mH, ⑤ This value determined from sample failure population, R_{G} = 25 $\!\Omega,\,I_{AS}$ = 35A, V_{GS} =10V. Part not recommended for use above this value.
- $\ensuremath{ \mbox{\scriptsize (3)}} \ I_{SD} \leq 35 A, \ di/dt \leq 380 A/\mu s, \ V_{DD} \leq V_{(BR)DSS},$ $T_J \le 175$ °C.
- ④ Pulse width \leq 1.0ms; duty cycle \leq 2%.
- ⑤ Coss eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- starting T_J = 25°C, L = 0.27mH, R_G = 25 Ω , I_{AS} = 35A, V_{GS} =10V
- This is applied to D²Pak, when mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- $\ensuremath{\$}\xspace$ R $_{\theta}$ is measured at T $_J$ approximately 90°C.
- 9 This is only applied to TO-220AB pakcage.

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ††					
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.					
Moistu	re Sensitivity Level	TO-220AB	N/A				
		D ² PAK	MSL1				
	Machine Model	Class M4					
		AEC-Q101-002					
50 D	Human Body Model	Class H1C					
ESD		AEC-Q101-001					
	Charged Device Model	Class C3					
		AEC-Q101-005					
RoHS Compliant		Yes					

- † Qualification standards can be found at International Rectifier's web site: http://www.irf.com/
- †† Exceptions to AEC-Q101 requirements are noted in the qualification report.

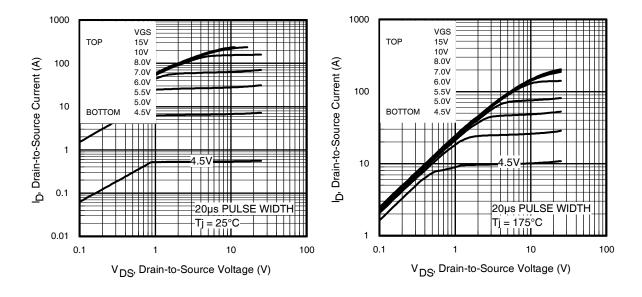


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

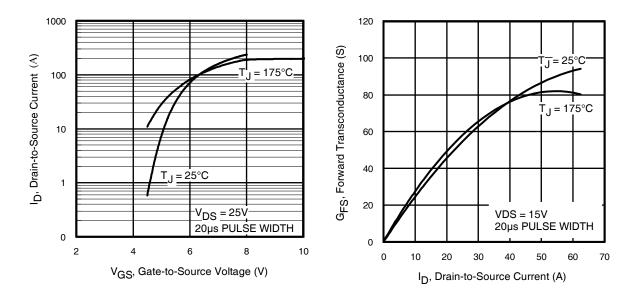
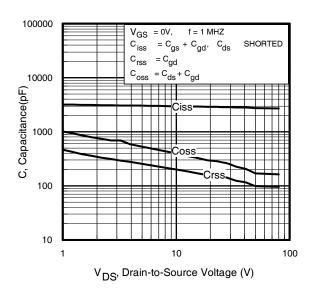


Fig 3. Typical Transfer Characteristics

Fig 4. Typical Forward Transconductance vs. Drain Current



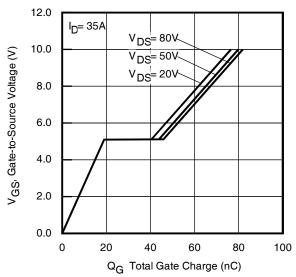
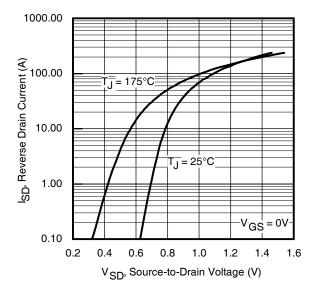


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage





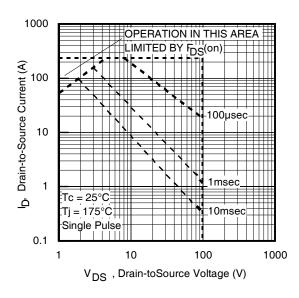


Fig 8. Maximum Safe Operating Area

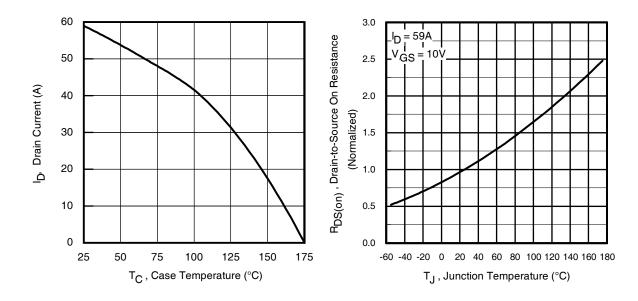


Fig 9. Maximum Drain Current vs. Case Temperature

Fig 10. Normalized On-Resistance vs. Temperature

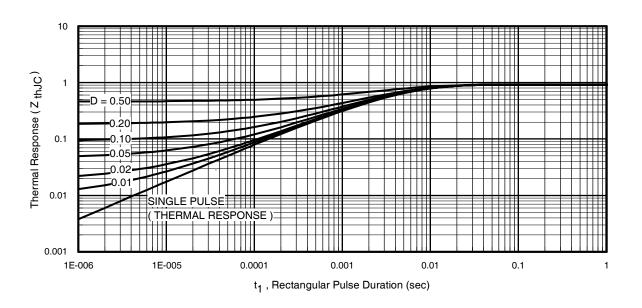


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

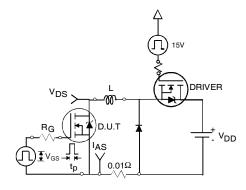


Fig 12a. Unclamped Inductive Test Circuit

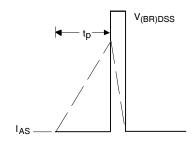


Fig 12b. Unclamped Inductive Waveforms

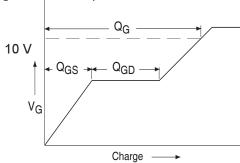


Fig 13a. Basic Gate Charge Waveform

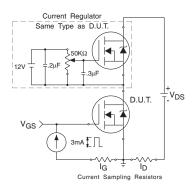


Fig 13b. Gate Charge Test Circuit

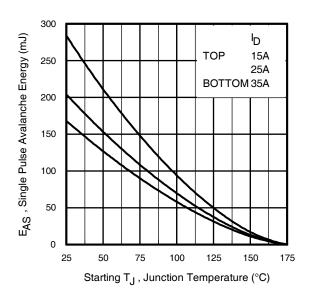


Fig 12c. Maximum Avalanche Energy vs. Drain Current

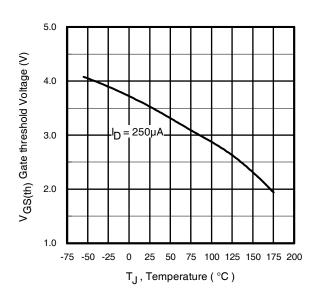


Fig 14. Threshold Voltage vs. Temperature

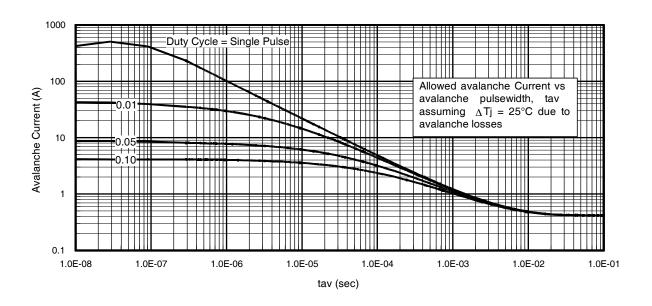


Fig 15. Typical Avalanche Current vs. Pulsewidth

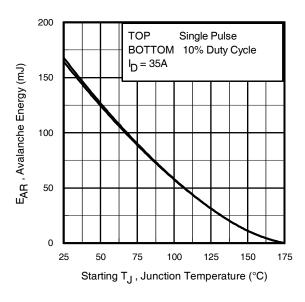


Fig 16. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16: (For further info, see AN-1005 at www.irf.com)

- 1. Avalanche failures assumption:
 - Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
- Safe operation in Avalanche is allowed as long asT_{jmax} is not exceeded.
- 3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
- 4. $P_{D (ave)}$ = Average power dissipation per single avalanche pulse.
- BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
- 6. I_{av} = Allowable avalanche current.
- 7. ΔT = Allowable rise in junction temperature, not to exceed T_{imax} (assumed as 25°C in Figure 15, 16).

t_{av =} Average time in avalanche.

 $D = Duty cycle in avalanche = t_{av} \cdot f$

 $Z_{th,IC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$\begin{split} P_{D \; (ave)} &= 1/2 \; (\; 1.3 \cdot BV \cdot I_{av}) = \triangle T / \, Z_{thJC} \\ I_{av} &= 2\triangle T / \, [1.3 \cdot BV \cdot Z_{th}] \\ E_{AS \; (AR)} &= P_{D \; (ave)} \cdot t_{av} \end{split}$$

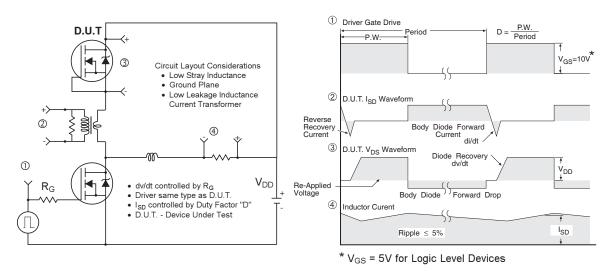


Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

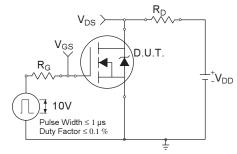


Fig 18a. Switching Time Test Circuit

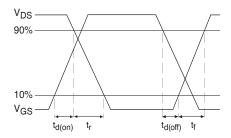
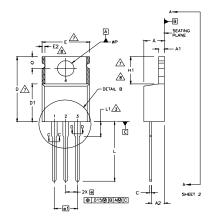
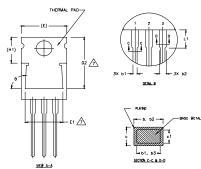


Fig 18b. Switching Time Waveforms

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)





SYMBOL

A1 A2 b b1 b2 b3

c c1

D D1 D2 E E1

e e1 H1 L L1 øP Q

- DIMENSIONING AND TOLERANCING PER ASME Y14.5 M— 1994, DIMENSIONIS ARE SHOWN IN INCHES [MILLIMETERS], LEAD DIMENSION AND FINISH UNCONTROLLED IN L1, DIMENSION D & E DO NOT INCLUDE MOLD FLASH, MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY, DIMENSION 1 & c1 APPLY TO BASE METAL ONLY. CONTROLLING DIMENSION : INCHES.

 THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1 DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.

MAX

4.82

2.92

1.01

0.96

1,77

0,61

16,51

9.02 12.88

10.66

8,89

6.35

3.42

INCHES

MAX.

.055

.040

.070

.355 .420 .350

.250

.135

4,7 7

7,8

MIN.

.020

.015

.045

,014

.560

.330

.380

.139

.100

MILLIMETERS

MIN,

3.56

0.51

0.38

0,38

1,15

0.36

8.38 12.19

9,66

8,38

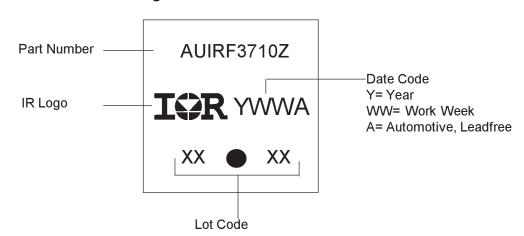
2.54

LEAD ASSIGNMENTS HEXFET

- 1,- GATE 2,- DRAIN 3,- SOURCE

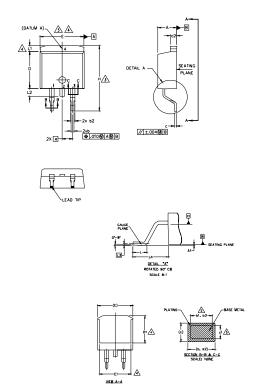
- DIODES
- 1.- ANODE/OPEN 2.- CATHODE 3.- ANODE

TO-220AB Part Marking Information



Note: For the most current drawing please refer to IR website at http://www.irf.com/package/ 10 www.irf.com

D²Pak Package Outline (Dimensions are shown in millimeters (inches))



- 1, DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3) DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
- 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
- 5. DIMENSION 61 AND c1 APPLY TO BASE METAL ONLY.
- 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 7, CONTROLLING DIMENSION; INCH,
- 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

S Y M B O L			Ŋ			
B	MILLIM	ETERS	INC	HES	NOTES	
L	MIN. MAX.		MIN.	MAX.	S	
Α	4.06	4.83	.160	.190		
Α1	0,00	0.254	.000	.010		
b	0.51	0.99	.020	.039		
ь1	0.51	0.89	.020	.035	5	
b2	1,14	1,78	.045	.070		
ь3	1,14	1,73	.045	.068	5	
С	0.38	0.74	.015	.029		
c1	0.38	0.58	.015	.023	5	
c2	1,14	1,65	.045	.065		
D	8.38	9.65	.330	.380	3	
D1	6.86	-	.270		4	
Ε	9.65	10.67	.380	.420	3,4	
E1	6,22	-	.245		4	
е	2.54	BSC	.100	.100 BSC		
Н	14.61	15.88	.575	.625		
L	1,78	2.79	.070	,110		
L1	-	1,65	-	.066	4	
L2	1.27	1.78	-	.070		
L3	0.25	BSC	.010 BSC			
L4	4.78	5.28	.188	.208		

LEAD ASSIGNMENTS

HEXFET

1.- GATE 2. 4.- DRAIN 3.- SOURCE

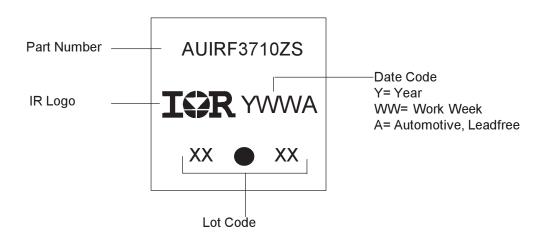
IGBTs, CoPACK

1.- GATE 2. 4.- COLLECTOR 3.- EMITTER

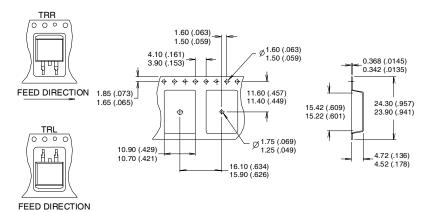
DIODES

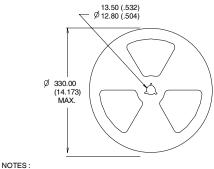
- * PART DEPENDENT.

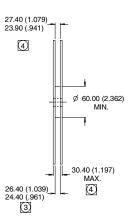
D²Pak Part Marking Information



D²Pak Tape & Reel Infomation







COMFORMS TO EIA-418.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION MEASURED @ HUB.
INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Ordering Information

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRF3710Z	TO-220	Tube	50	AUIRF3710ZS
AUIRF3710ZS	D2Pak	Tube	50	AUIRF3710ZS
AUIRF3710ZS		Tape and Reel Left	800	AUIRF3710ZSTRL
AUIRF3710ZS		Tape and Reel Right	800	AUIRF3710ZSTRR

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IR products are neither designed nor intended for use in automotive applications or environments unless the specific IR products are designated by IR as compliant with ISO/TS 16949 requirements and bear a part number including the designation "AU". Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, IR will not be responsible for any failure to meet such requirements.

For technical support, please contact IR's Technical Assistance Center http://www.irf.com/technical-info/

WORLD HEADQUARTERS:

233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

AMEYA360 Components Supply Platform

Authorized Distribution Brand:

























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QQ 800077892

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Tel +86 (21) 64016692-8333

Email mkt@ameya360.com